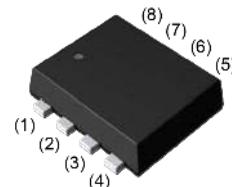


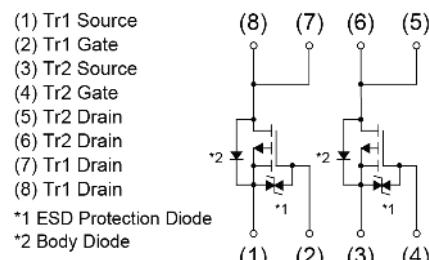
V_{DSS}	-12V
$R_{DS(on)}$ (Max.)	36m Ω
I_D	$\pm 4A$
P_D	1.5W

●Outline

TSMT8

**●Features**

- 1) Low on - resistance.
- 2) -1.5V Drive.
- 3) Built-in G-S protection diode.
- 4) Small surface mount package(TSMT8)
- 5) Pb-free lead plating ; RoHS compliant

●Inner circuit**●Packaging specifications**

Type	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TR
	Marking	J02

●Absolute maximum ratings ($T_a = 25^\circ C$) <It is the same ratings for the Tr1 and Tr2>

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	-12	V
Continuous drain current	I_D	± 4	A
Pulsed drain current	$I_{D,pulse}^{*1}$	± 12	A
Gate - Source voltage	V_{GSS}	± 10	V
Power dissipation	total	P_D^{*2}	1.5
	element		1.25
	total	P_D^{*3}	0.7
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	total	R_{thJA}^{*2}	-	-	83.3
	element		-	-	100
	total	R_{thJA}^{*3}	-	-	178

● Electrical characteristics ($T_a = 25^\circ\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = -1\text{mA}$	-12	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = -1\text{mA}$ referenced to 25°C	-	-21.9	-	$\text{mV}/^\circ\text{C}$
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -12\text{V}, V_{GS} = 0\text{V}$	-	-	-1	μA
Gate - Source leakage current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 10\text{V}$	-	-	± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = -6\text{V}, I_D = -1\text{mA}$	-0.3	-	-1.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = -1\text{mA}$ referenced to 25°C	-	2.4	-	$\text{mV}/^\circ\text{C}$
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	$V_{GS} = -4.5\text{V}, I_D = -4\text{A}$	-	26	36	$\text{m}\Omega$
		$V_{GS} = -2.5\text{V}, I_D = -2\text{A}$	-	36	50	
		$V_{GS} = -1.8\text{V}, I_D = -2\text{A}$	-	46	69	
		$V_{GS} = -1.5\text{V}, I_D = -0.8\text{A}$	-	66	132	
Gate input resistance	R_G	$f = 1\text{MHz}, \text{open drain}$	-	15	-	Ω
Forward Transfer Admittance	$ Y_{fs} ^{*4}$	$V_{DS} = -6\text{V}, I_D = -4\text{A}$	5.5	-	-	S

● Electrical characteristics ($T_a = 25^\circ\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$ $V_{DS} = -6\text{V}$ $f = 1\text{MHz}$	-	1940	-	pF
Output capacitance	C_{oss}		-	260	-	
Reverse transfer capacitance	C_{rss}		-	240	-	
Turn - on delay time	$t_{d(on)}^{\ast 4}$	$V_{DD} \approx -6\text{V}, V_{GS} = -4.5\text{V}$ $I_D = -2\text{A}$ $R_L = 3\Omega$ $R_G = 10\Omega$	-	10	-	ns
Rise time	$t_r^{\ast 4}$		-	60	-	
Turn - off delay time	$t_{d(off)}^{\ast 4}$		-	300	-	
Fall time	$t_f^{\ast 4}$		-	180	-	

● Gate charge characteristics ($T_a = 25^\circ\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	$Q_g^{\ast 4}$	$V_{DD} \approx -6\text{V}$ $I_D = -4\text{A}$ $V_{GS} = -4.5\text{V}$	-	20	-	nC
Gate - Source charge	$Q_{gs}^{\ast 4}$		-	3.5	-	
Gate - Drain charge	$Q_{gd}^{\ast 4}$		-	3.0	-	

● Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	I_S	$T_a = 25^\circ\text{C}$	-	-	-1	A
Body diode pulse current	$I_{SP}^{\ast 1}$		-	-	-12	
Forward voltage	$V_{SD}^{\ast 4}$	$V_{GS} = 0\text{V}, I_S = -4\text{A}$	-	-	-1.2	V

*1 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board (30x30x0.8mm)

*3 Mounted on a FR4 (20x20x0.8mm)

*4 Pulsed

● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

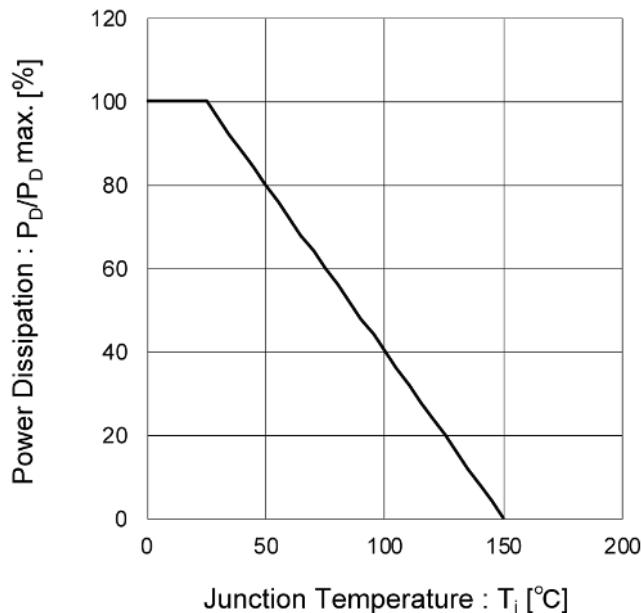


Fig.2 Maximum Safe Operating Area

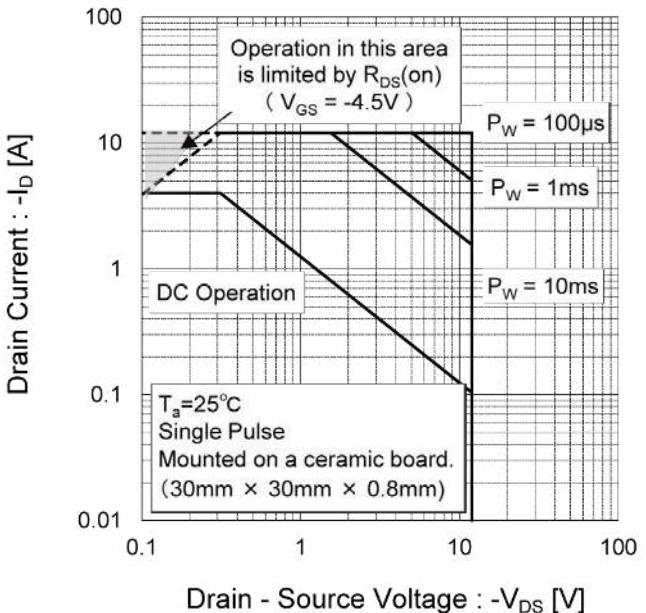


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

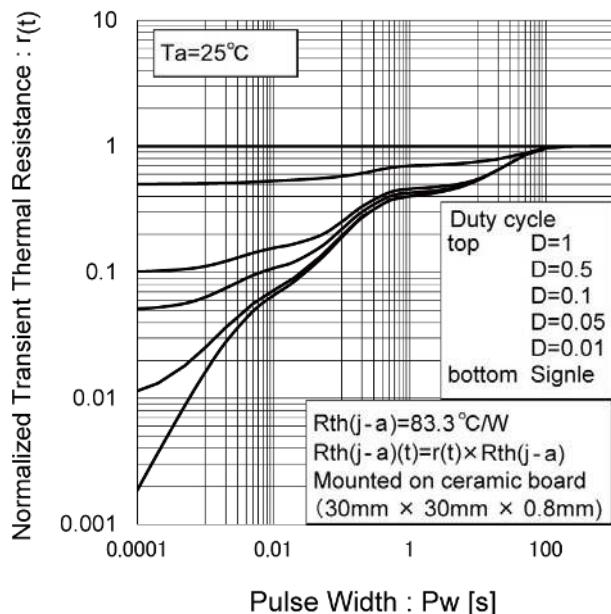
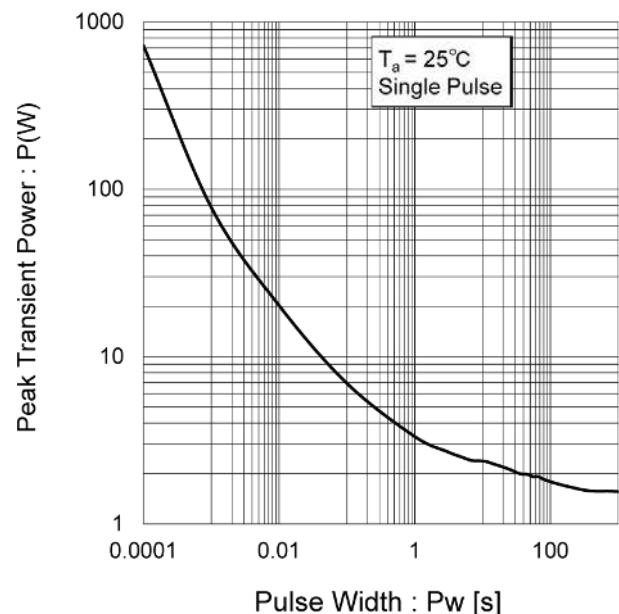


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

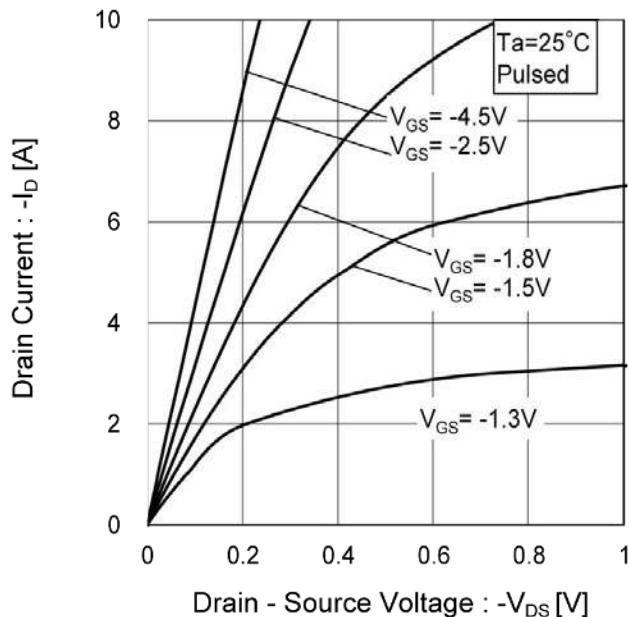


Fig.6 Typical Output Characteristics(II)

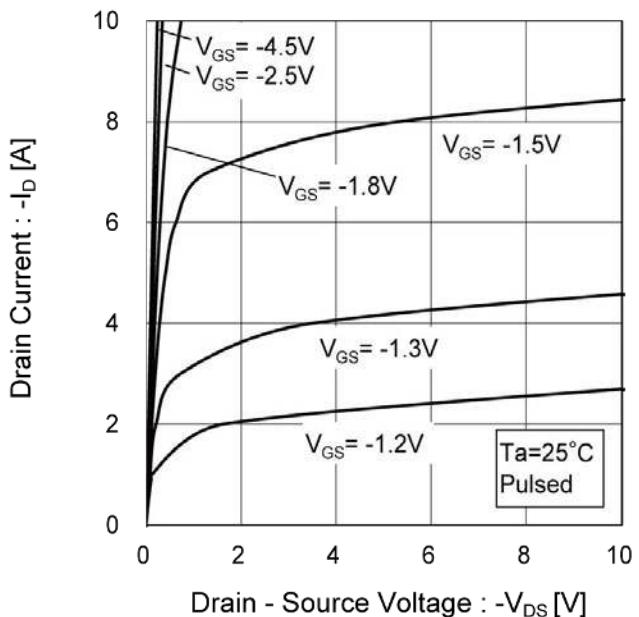
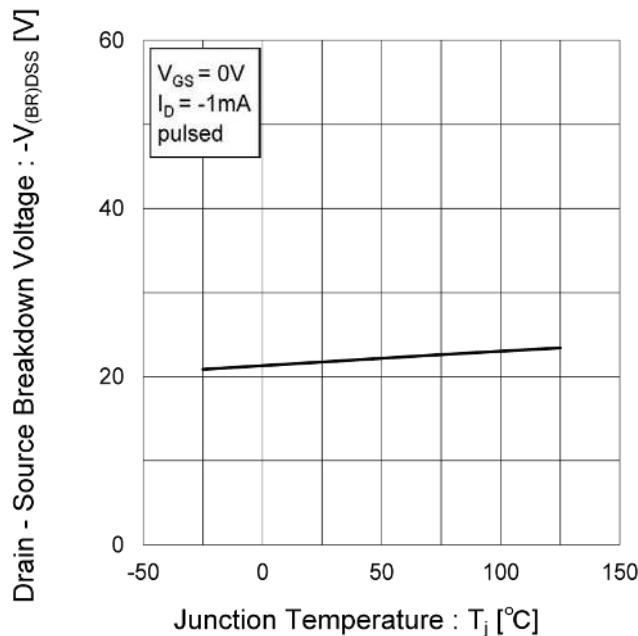
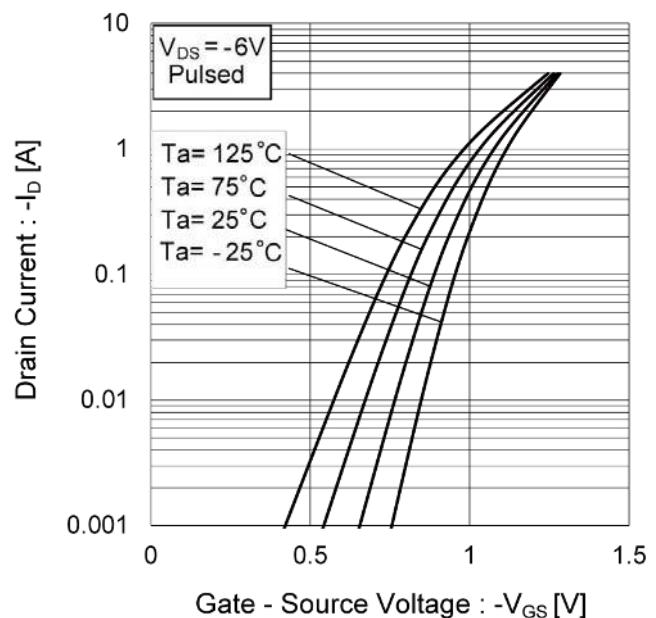
Fig.7 Breakdown Voltage vs.
Junction Temperature

Fig.8 Typical Transfer Characteristics



● Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs.
Junction Temperature

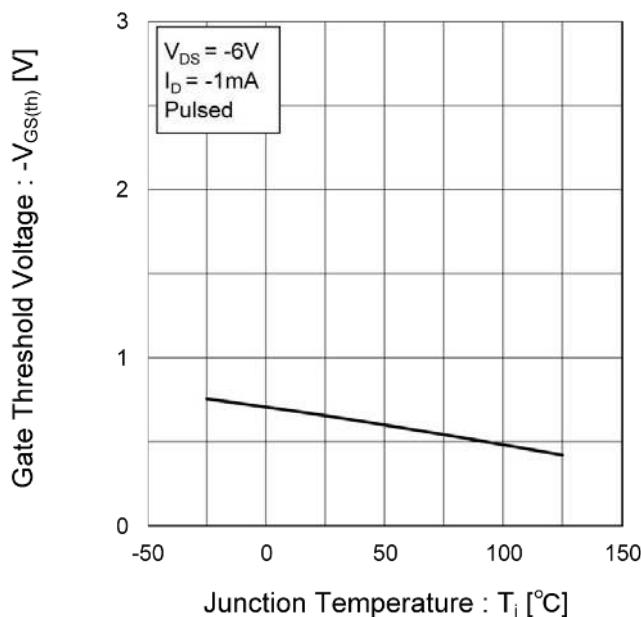


Fig.10 Forward Transfer Admittance vs.
Drain Current

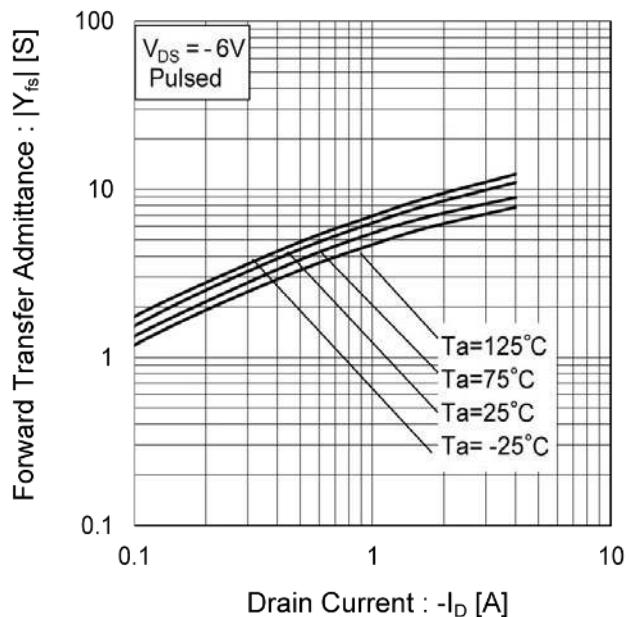


Fig.11 Drain Current Derating Curve

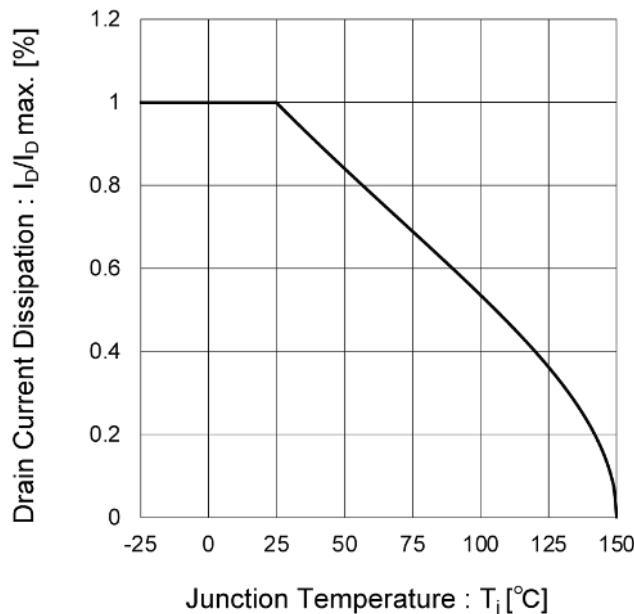
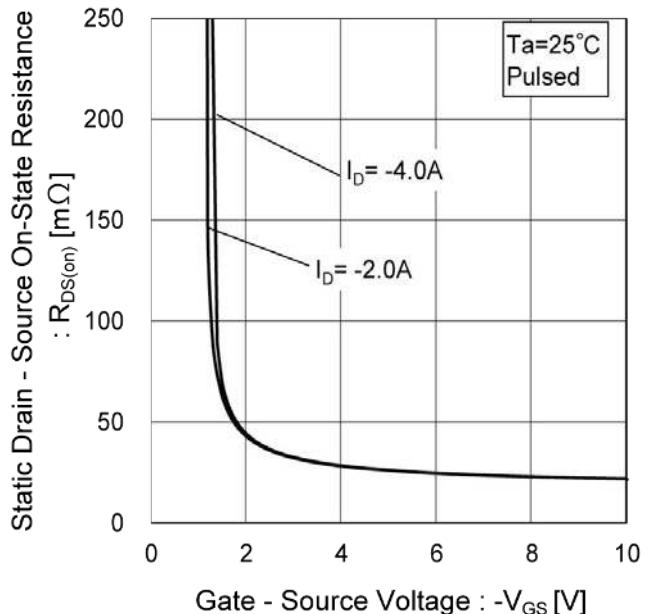


Fig.12 Static Drain - Source On - State
Resistance vs. Gate Source Voltage



●Electrical characteristic curves

Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature

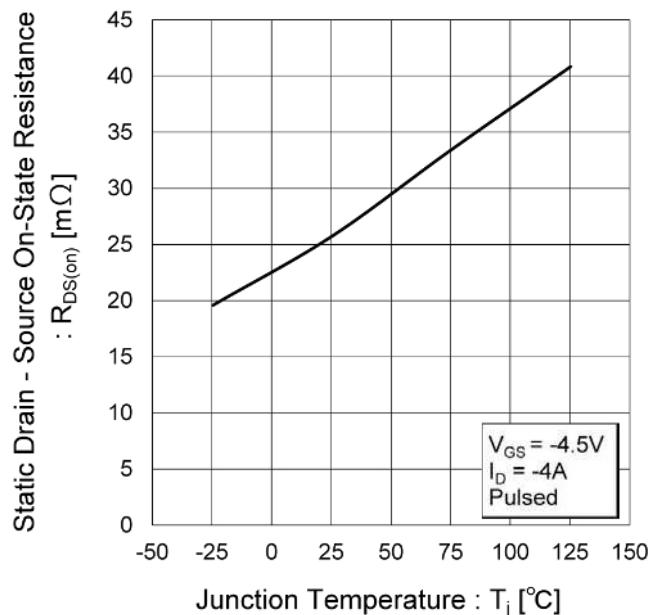
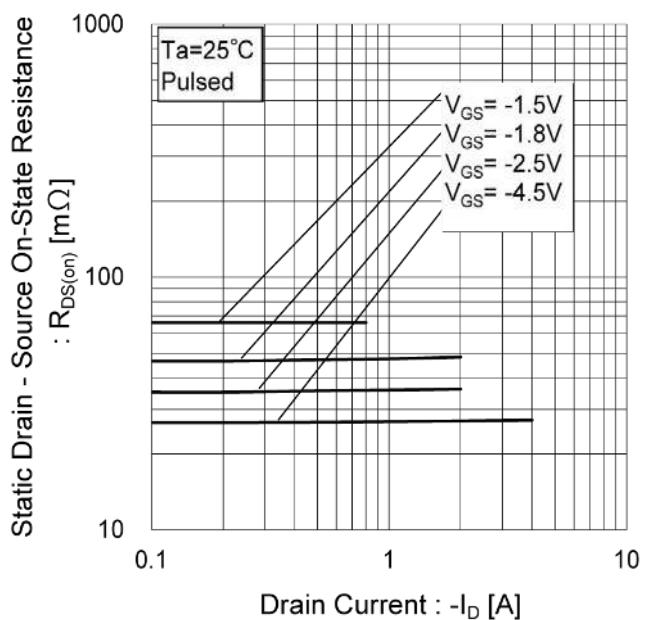


Fig.14 Static Drain - Source On - State
Resistance vs. Drain Current (I_D)



● Electrical characteristic curves

Fig.15 Static Drain - Source On - State
Resistance vs. Drain Current (II)

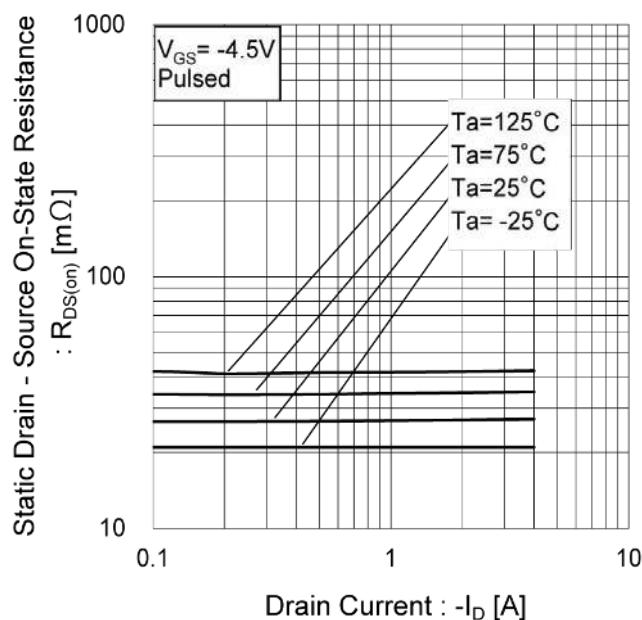


Fig.16 Static Drain - Source On - State
Resistance vs. Drain Current (III)

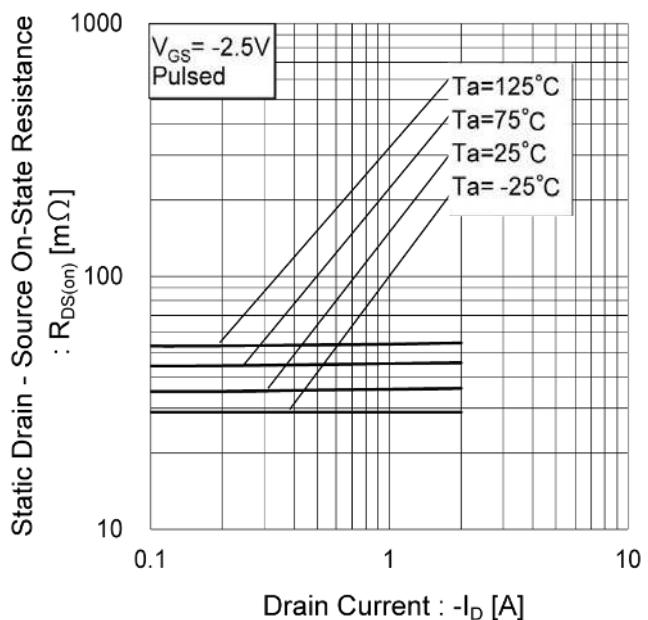


Fig.17 Static Drain - Source On - State
Resistance vs. Drain Current (IV)

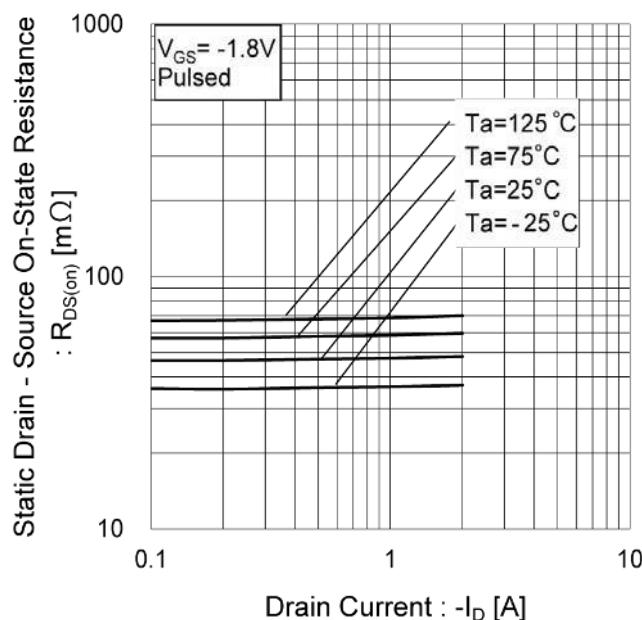
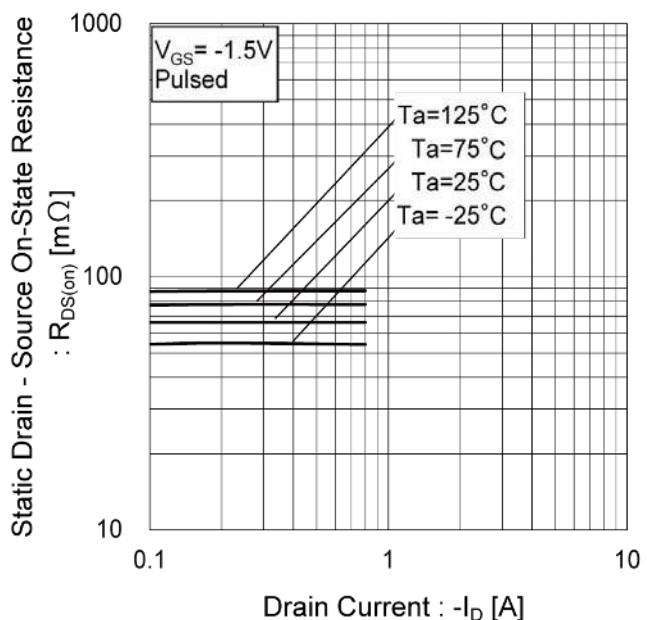


Fig.18 Static Drain - Source On - State
Resistance vs. Drain Current (V)



●Electrical characteristic curves

Fig.19 Typical Capacitance vs.
Drain - Source Voltage

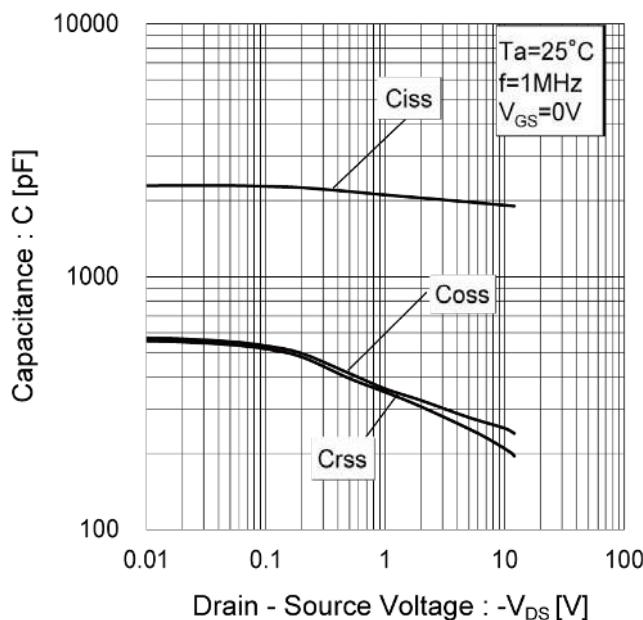


Fig.20 Switching Characteristics

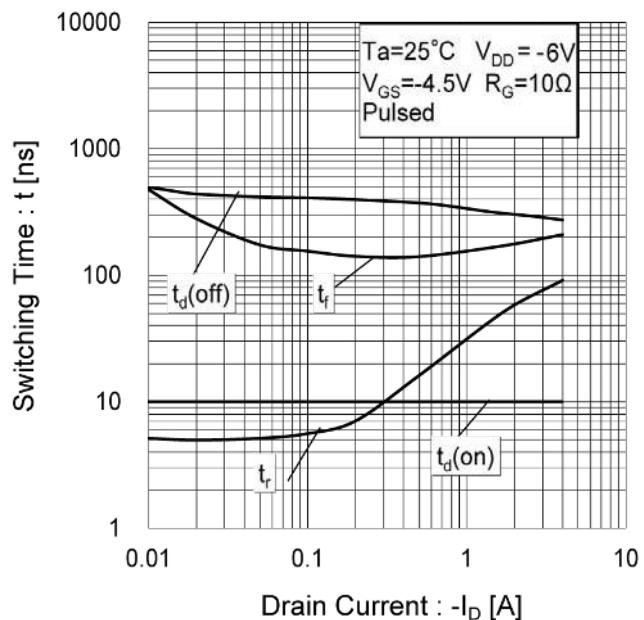


Fig.21 Dynamic Input Characteristics

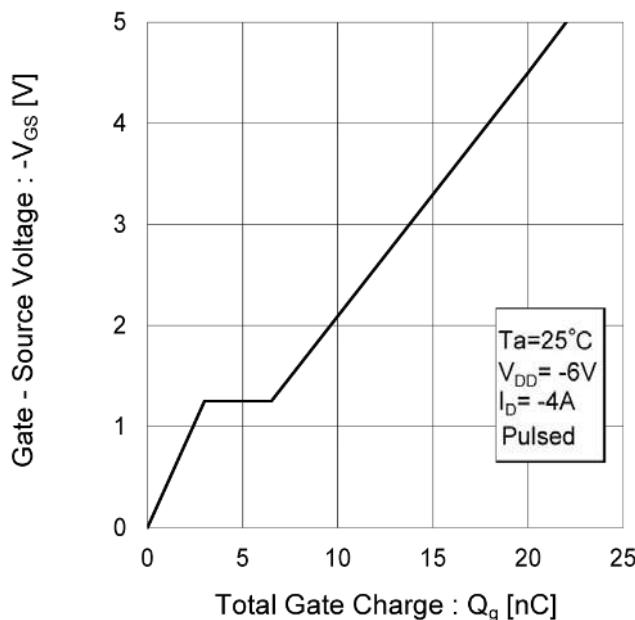
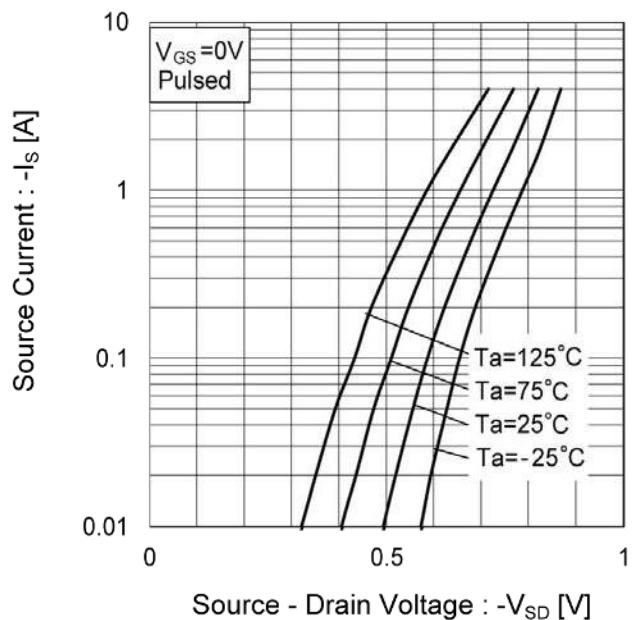


Fig.22 Source Current vs.
Source Drain Voltage



● **Measurement circuits <It is the same for the Tr1 and Tr2>**

Fig. 1-1 SWITCHING TIME MEASUREMENT CIRCUIT

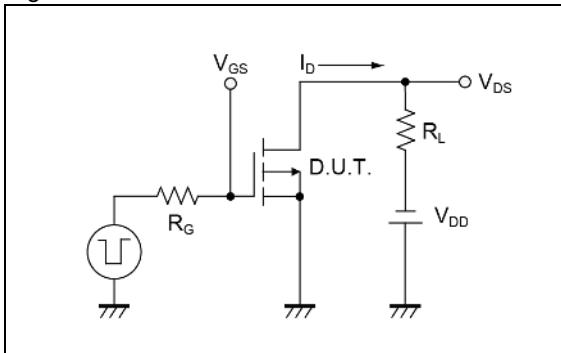


Fig. 1-2 SWITCHING WAVEFORMS

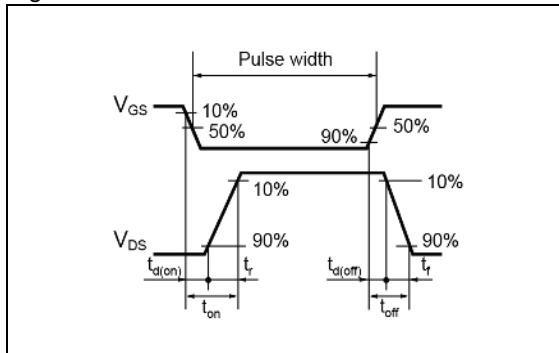


Fig. 2-1 GATE CHARGE MEASUREMENT CIRCUIT

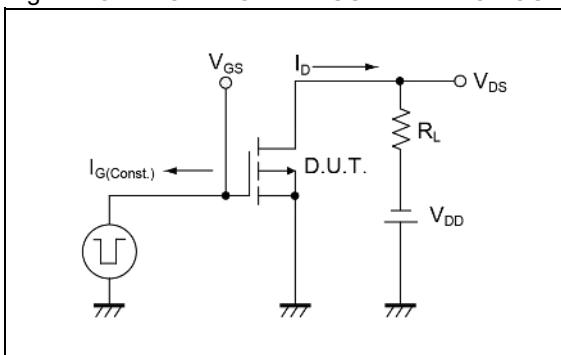
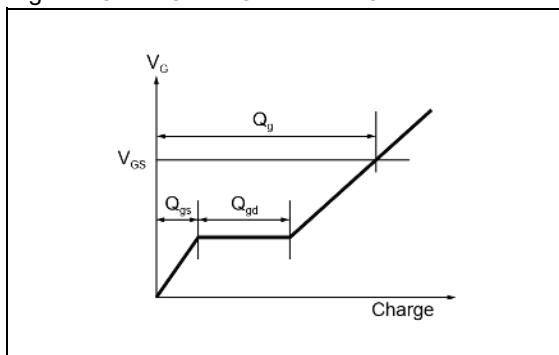


Fig. 2-2 GATE CHARGE WAVEFORM



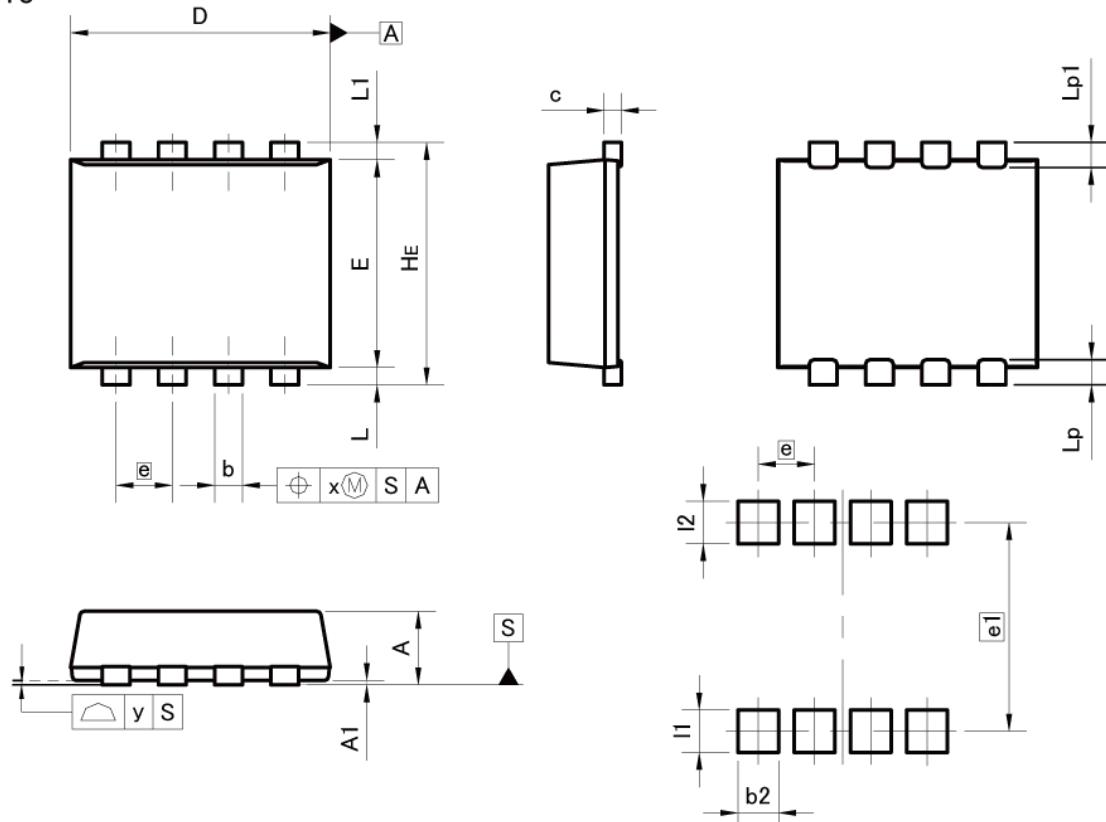
● **Notice**

This product might cause chip aging and breakdown under the large electrified environment.

Please consider to design ESD protection circuit.

●Dimensions

TSMT8



Pattern of terminal position areas
[Not a pattern of soldering pads]

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.030	0.033
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
c	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	2.30	2.50	0.091	0.098
e	0.65		0.026	
H _E	2.70	2.90	0.106	0.114
L	0.10	0.30	0.004	0.012
L1	0.10	0.30	0.004	0.012
L _p	0.19	0.39	0.007	0.015
L _{p1}	0.19	0.39	0.007	0.015
x	—	0.10	—	0.004
y	—	0.10	—	0.004

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b ₂	—	0.47	—	0.019
e ₁	2.41		0.095	
I ₁	—	0.49	—	0.019
I ₂	—	0.49	—	0.019

Dimension in mm/inches

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